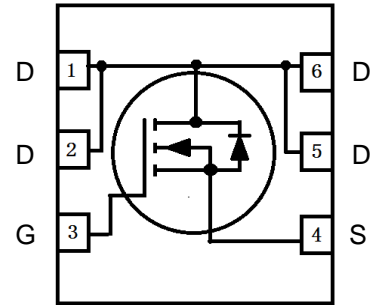
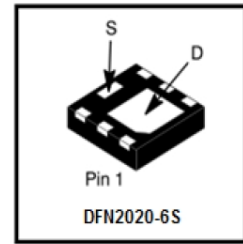


# S-LN3424DT2AG

## 30V N-Channel Enhancement MOSFET

### 1. FEATURES

- $V_{DS} = 30\text{ V}$   
 $R_{DS(ON)} \leq 10.5\text{ m}\Omega$ ,  $V_{GS}@10\text{ V}, I_{DS}@7\text{ A}$   
 $R_{DS(ON)} \leq 16.5\text{ m}\Omega$ ,  $V_{GS}@4.5\text{ V}, I_{DS}@5\text{ A}$
- Low  $R_{DS(ON)}$  trench technology
- Low thermal impedance
- Fast switching speed
- We declare that the material of product are Halogen Free and compliance with RoHS requirements.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



### 2. APPLICATIONS

- DC/DC Conversion
- Power Routing
- Motor Drives

### 3. ORDERING INFORMATION

Device	Marking	Shipping
S-LN3424DT2AG	2B	4000/Tape&Reel

### 4. MAXIMUM RATINGS(Ta = 25°C unless otherwise stated)

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDSS	30	V
Gate-to-Source Voltage		VGS	±20	V
Continuous Drain Current(Note 1)	TA =25°C	ID	12	A
	TA =70°C		9	
Pulsed Drain Current (Note 2)		IDM	48	A
Continuous Source Current (Diode Conduction)(Note 1)		IS	3.8	A
Power Dissipation(Note 1)	TA =25°C	PD	3	W
	TA =70°C		1.4	
Operating Junction and Storage Temperature Range		TJ , TSTG	-55 ~+150	°C

1.Surface Mounted on 1" x 1" FR4 Board.

2.Pulse width limited by maximum junction temperature.

### 5. THERMAL CHARACTERISTICS

Parameter		Symbol	Max	Unit
Maximum Junction-to-Ambient (Note 1)	t ≤10S	RθJA	40	°C/W
	Steady State		90	

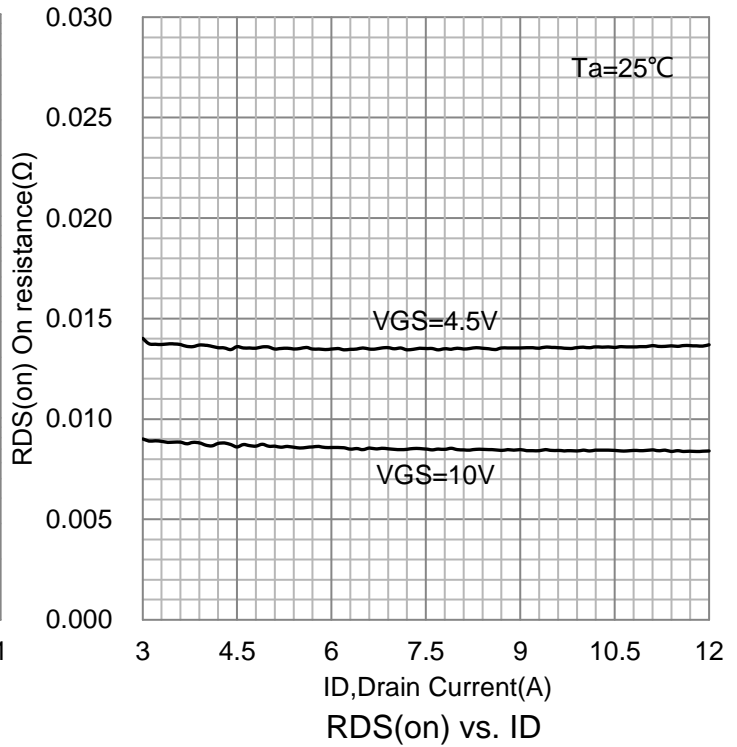
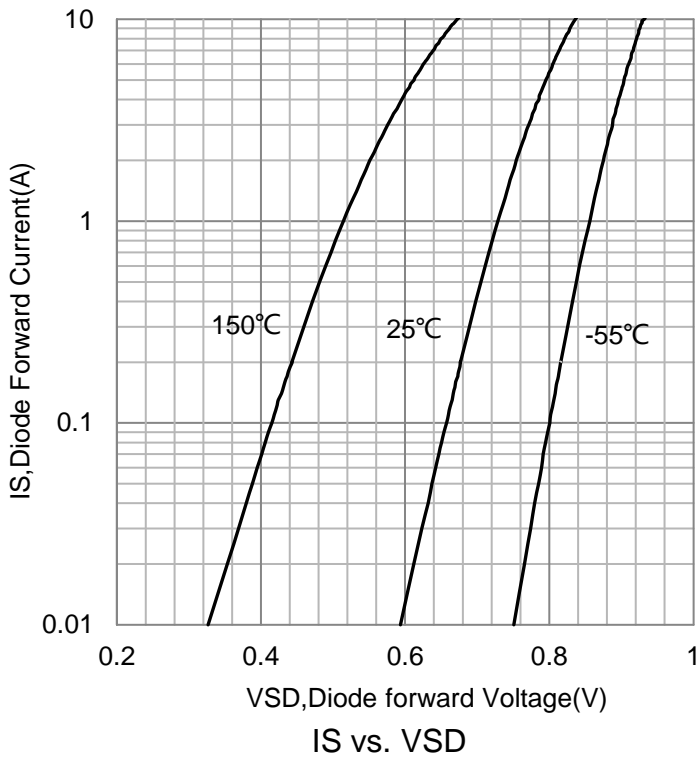
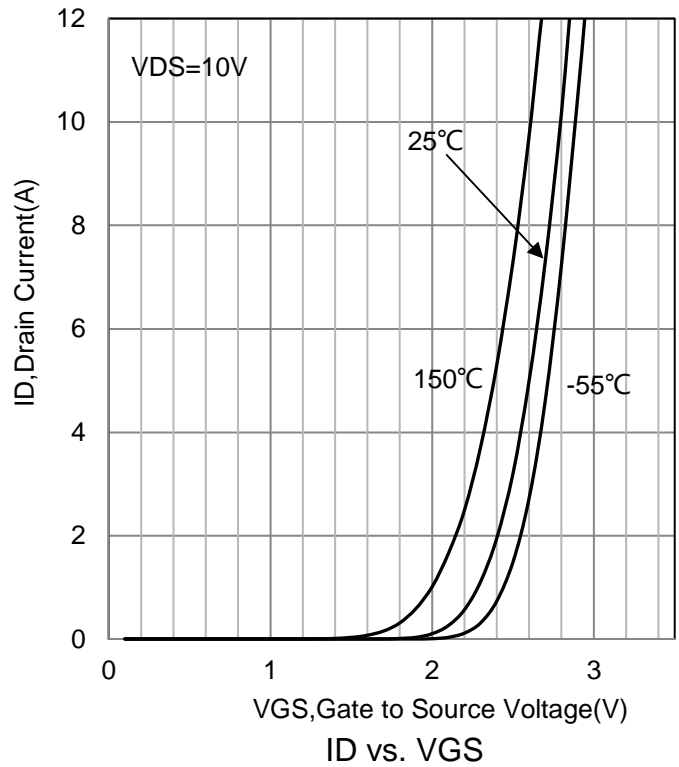
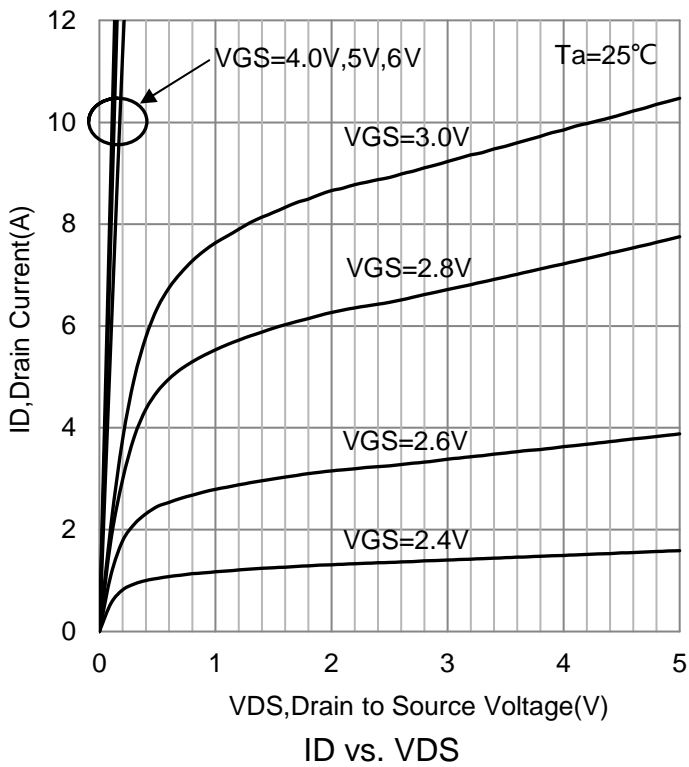
## 6. ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit	
Static						
Drain to Source Breakdown Voltage (VGS = 0V, ID = 250μA)	V(BR)DSS	30	-	-	V	
Gate-Source Threshold Voltage (VDS = VGS, ID = 250μA)	VGS(th)	1	1.6	1.8	V	
Gate-Body Leakage (VDS = 0 V, VGS = ±20 V)	IGSS	-	-	±100	nA	
Zero Gate Voltage Drain Current (VDS = 24 V, VGS = 0 V) (VDS = 24 V, VGS = 0 V, TJ = 55°C)	IDSS	-	-	1 25	μA	
Drain-Source On-Resistance(Note 3) (VGS = 10 V, ID = 7 A) (VGS = 4.5 V, ID = 5 A)	RDS(on)	-	8 13.5	10.5 16.5	mΩ	
Diode Forward Voltage(Note 3) (IS = 1.9 A, VGS = 0 V)	VSD	-	0.9	1.5	V	
Dynamic(Note 4)						
Total Gate Charge	(VDS = 15 V, VGS = 4.5 V, ID = 6 A)	Qg	-	11	-	nC
Gate-Source Charge		Qgs	-	3.2	-	
Gate-Drain Charge		Qgd	-	4.3	-	
Turn-On Delay Time	(VDS = 15 V, RL=1.4 Ω, ID = 6 A, VGEN = 10 V, RGEN = 6 Ω)	td(on)	-	6	-	ns
Rise Time		tr	-	6	-	
Turn-Off Delay Time		td(off)	-	29	-	
Fall Time		tf	-	8	-	
Input Capacitance	(VDS = 15 V, VGS = 0 V, f = 1 Mhz)	Ciss	-	1136	-	pF
Output Capacitance		Coss	-	133	-	
Reverse Transfer Capacitance		Crss	-	119	-	
Gate-Resistance (VGS = 0 V, VDS=0V, f=1MHz)	Rg	-	0.72	-	Ω	

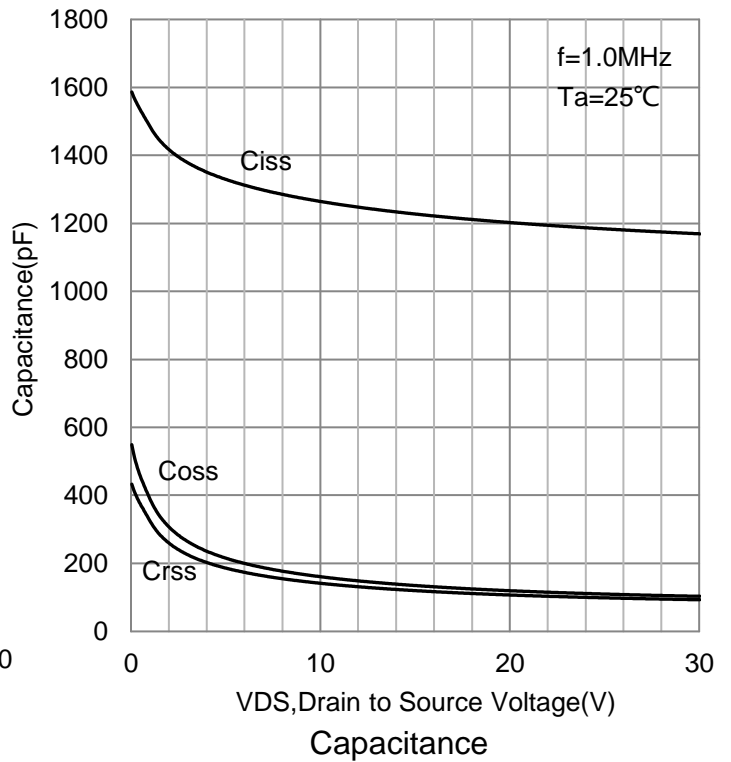
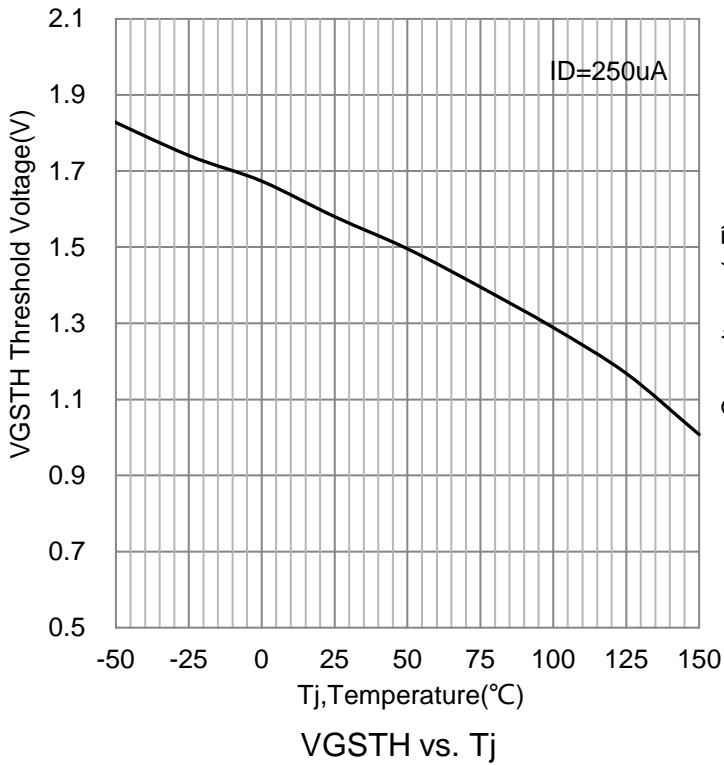
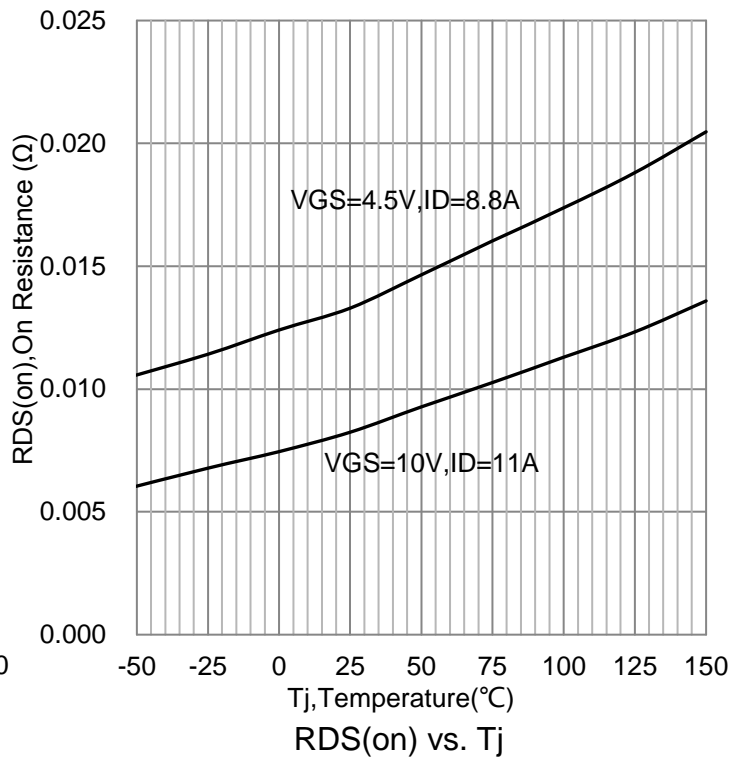
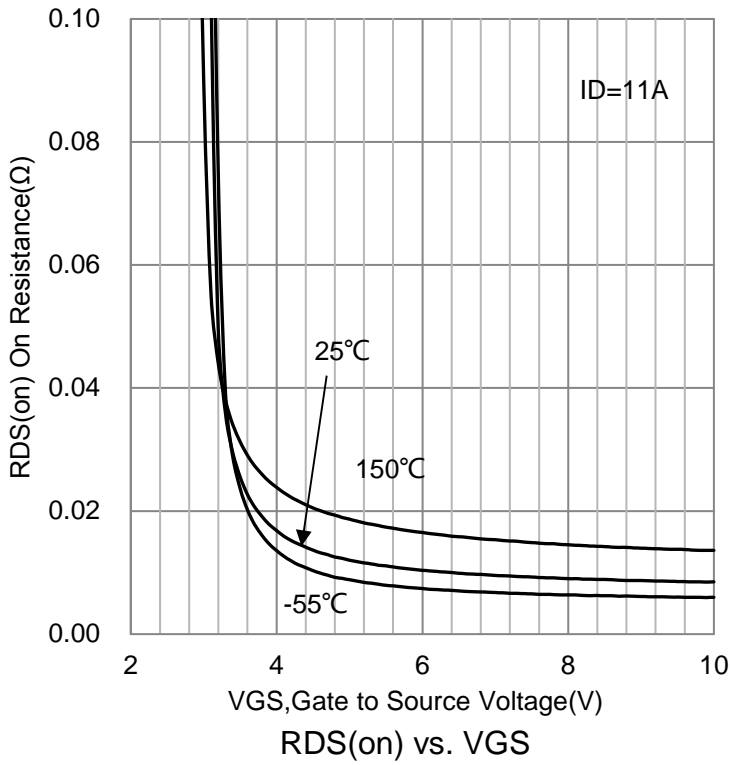
3. Pulse test: PW ≤ 300us duty cycle ≤ 2%.

4. Guaranteed by design, not subject to production testing.

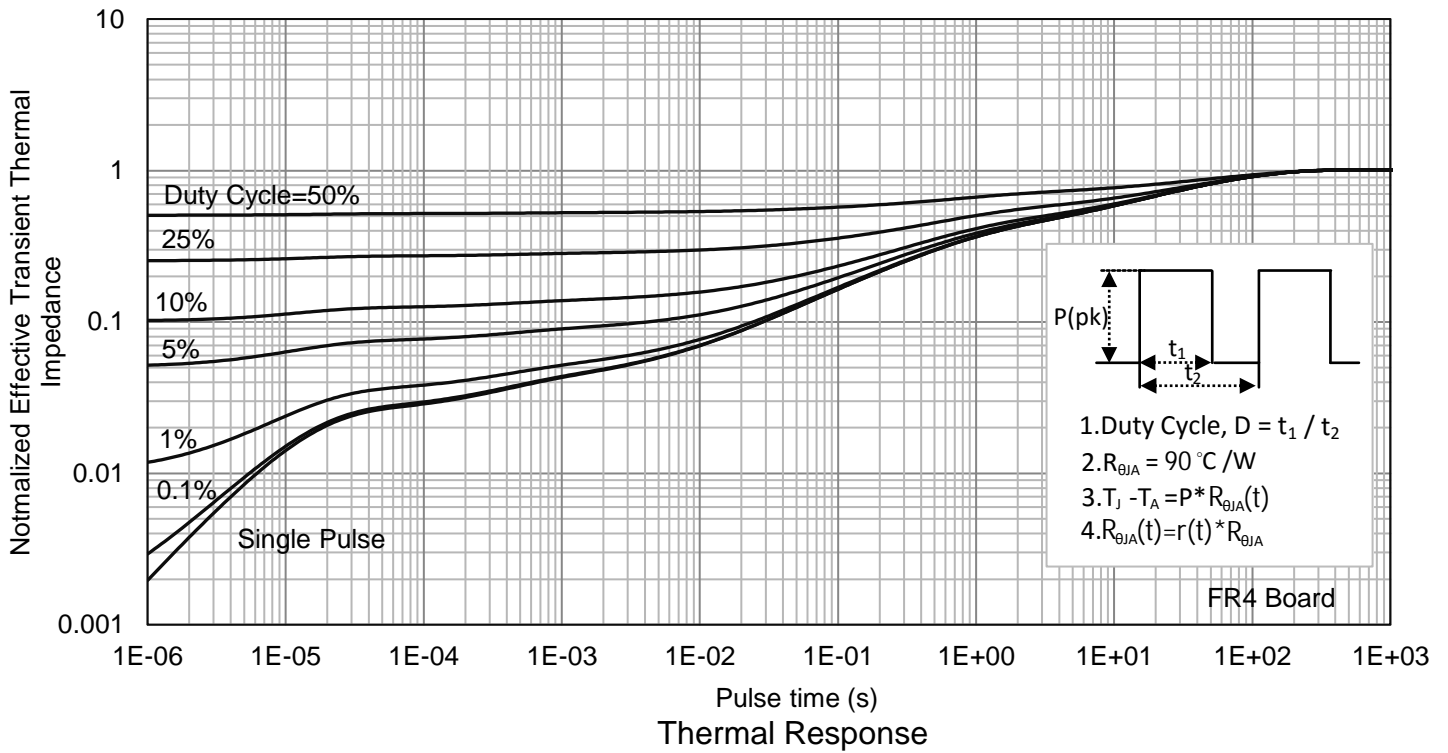
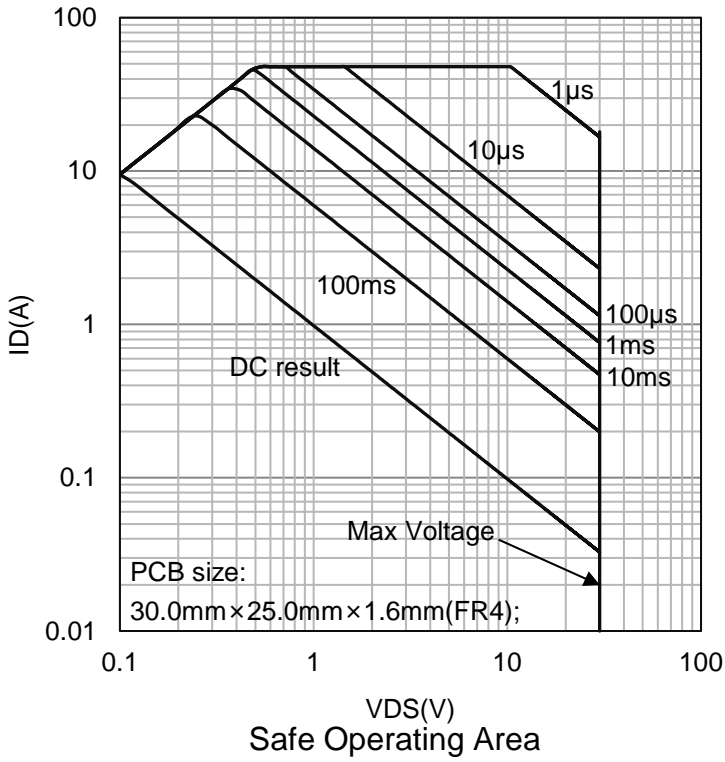
**7.ELECTRICAL CHARACTERISTICS CURVES**



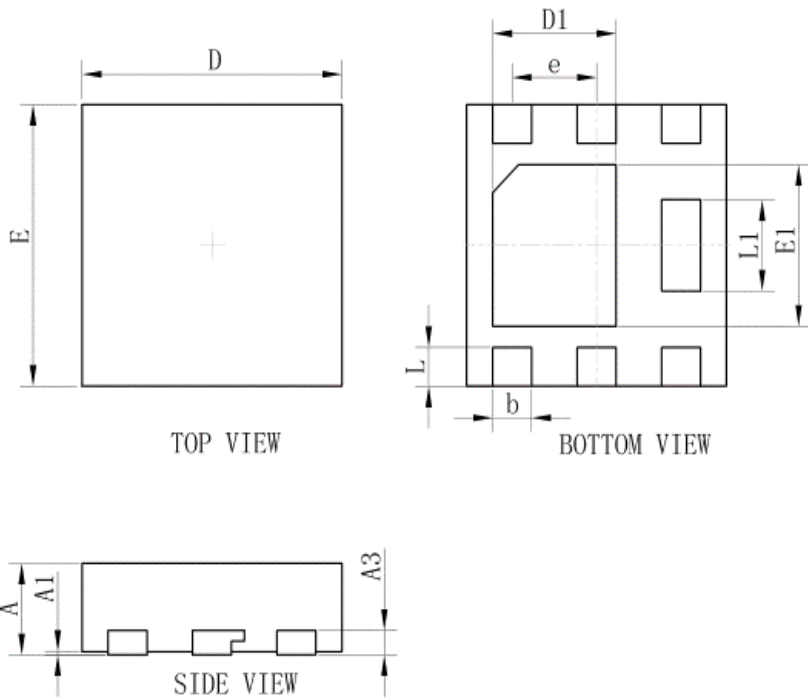
**7.ELECTRICAL CHARACTERISTICS CURVES(Con.)**



**7.ELECTRICAL CHARACTERISTICS CURVES(Con.)**

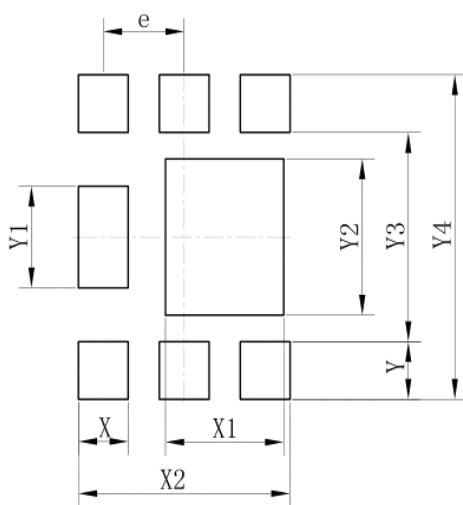


### 8. OUTLINE AND DIMENSIONS



DFN2020-6S			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.01	0.03	0.05
b	0.25	0.30	0.35
D	1.95	2.00	2.05
E	1.95	2.00	2.05
e	0.65TYP.		
L	0.23	0.28	0.33
L1	0.60	0.65	0.65
D1	0.90	0.95	1.00
E1	1.10	1.15	1.20
A3	0.152REF		
All Dimensions in mm			

### 9. SOLDERING FOOTPRINT



DFN2020-6S	
Dim	(mm)
X	0.40
X1	0.95
X2	1.70
e	0.65
Y	0.43
Y1	0.75
Y2	1.15
Y3	1.54
Y4	2.39